

Abstract

The present invention relates to a non-volatile memory comprising: a first electrode (11); a second electrode (12); and a phase-change recording medium (14) sandwiched between the first electrode (11) and the second electrode (12), in which resistance value is varied by applying an electrical pulse across the first electrode (11) and the second electrode (12), at least one of the first electrode (11) and the second electrode (12) contains as a main ingredient at least one member selected from the group consisting of ruthenium, rhodium and osmium, and the phase-change recording medium (14) is formed of a phase-change material that contains chalcogen(s). This non-volatile memory exhibits improved durability and reliability by preventing deterioration of property (i.e., mutual impurity diffusion between the electrode and the phase-change recording medium) caused by application of current.